

The BA6589K IC incorporates read, write, and erase circuits for use with 3 in., 3.5 in., and 5 in. floppy disk drives.

It can be operated at either 5 V or 12 V. It has a power save mode which ensures the IC has a very low average current draw.

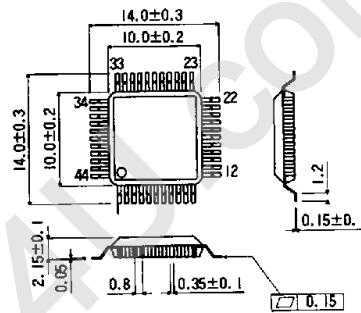
### Features

- available in a QFP44 package
- low power consumption, typically
  - read mode is 250 mW
  - write mode is 90 mW
  - standby (power save) mode is 12 mW
- preamplifier differential voltage gain is 47.5 dB (5 V operation)
- includes a capacitor to set up the read data time constant and the pulse width
- includes a switching differential constant circuit
- write current is selectable as follows:
  - double density inner track
  - double density outer track
  - high density inner track
  - high density outer track
- selectable two-stage time domain filter
- includes a low voltage sensing circuit to avoid miswrites due to voltage fluctuations

### Applications

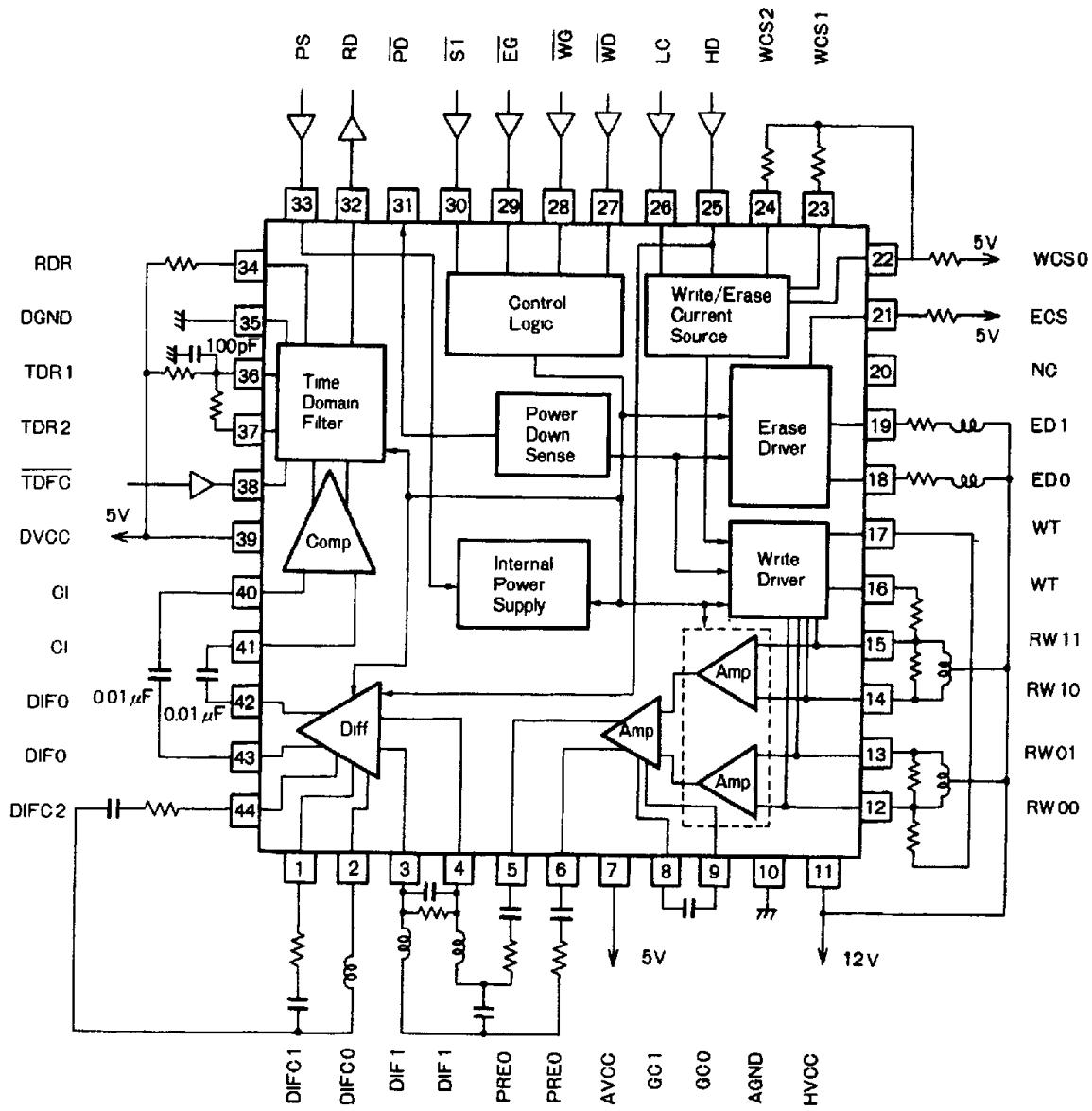
- 3 in., 3.5 in., and 5 in. high- or double density floppy disk drives

### Dimensions (Units : mm)

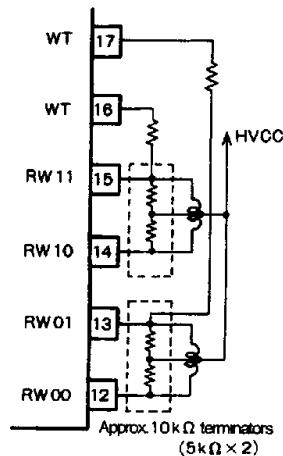
**BA6589K (QFP44)**

## BA6589K Floppy disk drives: Read/write amplifier

### Block diagram and external circuit



**Note:** Depending on the read/write head characteristics, when the write current switches, the current waveform may tend to cause oscillation (especially if the phase inverts at a frequency approaching 2 MHz). In this situation, use a circuit such as the one shown to the right, and check for oscillations.



**Table 1 Pin functions**

Function	Pin no.	Symbol	Description
Head switching count	12, 13	RW00, RW01	Connections for side 0 read/write head
	14, 15	RW10, RW11	Connections for side 1 read/write head
Read preamp	9, 8	GC0, GC1	Gain adjust pins
	6, 5	PREO	Preamplifier differential outputs
Differentiator	4, 3	DIF1	Differentiator differential inputs
	2	DIFCO	Connections for external differentiator circuit constant components
	1	DIFC1	
	44	DIFC2	
Comparator	43, 42	DIF0	Differentiator differential outputs
	41, 40	C1	Comparator differential inputs
Time domain filter	37	TDR2	Connection point for time domain filter time constant
	36	TDR1	Pin to set time domain filter
	34	RDR	Pin to set read data output pulse width
	32	RD	Read data output
Write circuit	22	WCS0	Pin to set write current
	23	WCS1	Write current correction pin 1 (Valid when LC pin is HIGH)
	24	WCS2	Write current correction pin 2 (Valid when HD pin is HIGH)
	16, 17	WT	Connection point for write damping resistor
Erase circuit	18	ED0	Side 0 erase output
	19	ED1	Side 1 erase output
	21	ECS	Pin to set erase current
Control logic input	25	HD	Standard density- to-high density switching pin (see note 1 on page 250).
	26	LC	Track inner/outer switching pin (see note 1 on page 250).
	27	WD	Write data input
	8	WG	Write enable input
	29	EG	Erase enable input
	30	S1	Input to switch head side
	33	PS	Power save mode input
	38	TDFC *3	Input to switch time domain filter constants (see note 2 on page 250).
Power-down sense	31	PD	Power down sense output
Power supply	11	HVCC	Preamplifier supply voltage
	7	AVCC	Analog circuit supply voltage
	39	DVCC	Digital circuit supply voltage
	10	AGND	Analog circuit ground
	35	DGND	Digital circuit ground
	20	NC	Not used

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### Note 1:

HD	LC	Write current	Differentiator constants
HIGH	HIGH	Current set by pins 22, 23, and 24	Circuit constants between pins 44 and 2 are in effect.
	LOW	Current set by pins 22 and 24	
LOW	HIGH	Current set by pins 22 and 23	Circuit constants between pins 1 and 2 are in effect.
	LOW	Current set by pin 22	

**Note 2:** Correction applied when pin is HIGH. External correction resistors are placed in parallel with the primary resistances to set the values.

### Absolute maximum ratings ( $T_a = 25^\circ\text{C}$ )

Parameter	Symbol	Limits	Unit
Power supply voltage	$\text{AV}_{\text{CC}}$	+7	V
	$\text{DV}_{\text{CC}}$	+7	V
	$\text{HV}_{\text{CC}}$	+16	V
Digital circuit input voltage	$\text{V}_I$	-0.3 ~ $\text{DV}_{\text{CC}} + 0.3$	V
RW pin voltage	$\text{V}_{\text{RW}}$	+25	V
PD pin output voltage	$\text{V}_{\text{PD}}$	+16	V
Erase drive current	$\text{I}_{\text{ER}}$	100	mA
EO pin voltage	$\text{V}_{\text{ER}}$	+25	V
Operating temperature	$\text{T}_{\text{opr}}$	0 ~ +70	$^\circ\text{C}$
Storage temperature	$\text{T}_{\text{stg}}$	-55 ~ +125	$^\circ\text{C}$

### Recommended operating conditions ( $T_a = 0^\circ\text{C} \sim 70^\circ\text{C}$ )

Parameter	Symbol	Min	Typical	Max	Unit
Power supply voltage	$\text{AV}_{\text{CC}}$	4.4	5.0	6.0	V
	$\text{DV}_{\text{CC}}$	4.4	5.0	6.0	V
	$\text{HV}_{\text{CC}}$	10.8	12.0	13.2	V

**Electrical characteristics (unless otherwise noted,  $T_a = 25^\circ\text{C}$ ,  $\text{AV}_{\text{CC}} = \text{DV}_{\text{CC}} = 5 \text{ V}$ ,  $\text{HV}_{\text{CC}} = 12 \text{ V}$ ) (Sheet 1 of 5)**

Parameter	Symbol	Min	Typical	Max	Unit	Conditions	Test circuit
<b>Supply current</b>							
Supply current, standby	$I_{\text{CCHS}}$		0.33	0.80	mA	@ $\text{HV}_{\text{CC}}$	Fig. 3
	$I_{\text{CCDS}}$		0.82	1.3	mA	@ $\text{DV}_{\text{CC}}$	
	$I_{\text{CCAS}}$		0.8	1.3	mA	@ $\text{AV}_{\text{CC}}$	
Supply current, read	$I_{\text{CCHR}}$		5.80	8.10	mA	@ $\text{HV}_{\text{CC}}$	
	$I_{\text{CCDR}}$		20.0	28.0	mA	@ $\text{DV}_{\text{CC}}$	
	$I_{\text{CCAR}}$		17	23.5	mA	@ $\text{AV}_{\text{CC}}$	
Supply current, write	$I_{\text{CCHW}}$		0.60	1.20	mA	@ $\text{HV}_{\text{CC}}$ , $I_{\text{WR}} = I_{\text{ER}} = 0 \text{ mA}$	
	$I_{\text{CCDW}}$		10	18	mA	@ $\text{DV}_{\text{CC}}$ , $I_{\text{WR}} = I_{\text{ER}} = 0 \text{ mA}$	
	$I_{\text{CCAW}}$		7.0	10	mA	@ $\text{AV}_{\text{CC}}$ , $I_{\text{WR}} = I_{\text{ER}} = 0 \text{ mA}$	
<b>Low voltage sensing circuit</b>							
Threshold voltage	$V_{\text{TH}}$	3.5	3.9	4.2	V	LVS @ $\text{AV}_{\text{CC}}$	Fig. 4
Hysteresis voltage	$V_H$	50			mV		
Output low level voltage	$V_{\text{OL}}$			0.4	V	$\text{V}_{\text{CC}} = 2 \text{ V}$ , $I_{\text{OL}} = 0.5 \text{ mA}$	
Output leakage current	$I_{\text{OH}}$			1	$\mu\text{A}$		
<b>Recovery time</b>							
Power save → read	$t_{\gamma 1}$			1	ms	Invoked by PS: With 0.01 $\mu\text{F}$ coupling capacitors between differentiator and comparator, and <1 $\mu\text{F}$ capacitors from differentiator input to GND	Fig. 5
Read → write	$t_{\gamma 2}$			4	$\mu\text{s}$	Invoked by $\overline{\text{WG}}$ : Circuit constant capacitors (pin 44↔2 & pin 1↔2) are <0.01 $\mu\text{F}$	
Write → read	$t_{\gamma 3W}$			300	$\mu\text{s}$	Invoked by $\overline{\text{WG}}$	
	$t_{\gamma 3E}$			20	$\mu\text{s}$	Invoked by $\overline{\text{EG}}$	
Side0 ↔ Side1	$t_{\gamma 4}$			40	$\mu\text{s}$	Invoked by $\overline{\text{S1}}$	
<b>Preamplifier</b>							
Diff. output voltage gain	$G_{\text{VD}}$	46	49	52	dB	$f = 250 \text{ kHz}$ , $V_{\text{IN}} = 2.5 \text{ mV}_{\text{pk-pk}}$	Fig. 6
Frequency characteristic	$\text{BW}$	3			mHz	$250 \text{ kHz} = 0 \text{ dB}, -3 \text{ dB}$	
Crosstalk side0 ↔ side1	$G_{\text{CTLK}}$	50			dB	$f = 250 \text{ kHz}$	
Diff. input resistance	$R_{\text{ID}}$	20			$\text{k}\Omega$		Fig. 7

## BA6589K Floppy disk drives: Read/write amplifier

**Electrical characteristics (unless otherwise noted,  $T_a = 25^\circ\text{C}$ ,  $\text{AV}_{\text{CC}} = \text{DV}_{\text{CC}} = 5 \text{ V}$ ,  $\text{HV}_{\text{CC}} = 12 \text{ V}$ ) (Sheet 2 of 5)**

Parameter	Symbol	Min	Typical	Max	Unit	Conditions	Test circuit
Input conversion noise voltage (1)	$V_{N1}$		4.5	8	$\mu\text{V}_{\text{rms}}$	$f = 400 \sim 1 \text{ MHz}$	Fig. 8
Input conversion noise voltage (2)	$V_{N2}$		5	10	$\mu\text{V}_{\text{rms}}$	$f = 400 \sim 1 \text{ MHz}$ , Measured with $1 \text{ V}_{\text{pk-pk}}, 250 \text{ kHz}$ signal applied to differentiator input. TDF pulse width = $1.2 \mu\text{s}$ ; RD pulse width = $0.5 \mu\text{s}$	
Input sink current	$I_{\text{SINK}}$		100	200	$\mu\text{A}$		Fig. 9
Diff. input voltage max amplitude	$V_{\text{INmax}}$			15	$\text{mV}_{\text{pk-pk}}$	Includes measurements made with correction resistor between pins 8 & 9	Fig. 6
Diff. output voltage amplitude	$V_{\text{OD}}$	2			$\text{V}_{\text{pk-pk}}$	Distortion rate = 5%	
Diff. output resistance	$R_{\text{OD}}$		120		$\Omega$		
Diff. output current amplitude	$I_{\text{OD}}$	5.8	7.4		$\text{mA}_{\text{pk-pk}}$		
Common mode rejection ratio	CMRR	50			dB	$L = 330 \mu\text{H}, f = 250 \text{ kHz}$ , $V_{\text{IN}} = 100 \text{ mV}_{\text{pk-pk}}$	Fig. 10
Power supply rejection ratio	PSRR	60			dB	$L = 330 \mu\text{H}, f = 125 \text{ kHz}$	Fig. 11
		40			dB	$V_{\text{IN}} = 100 \text{ mV}_{\text{pk-pk}}, f = 400 \text{ kHz}$	
<b>Differentiator</b>							
Voltage gain	$G_{\text{VD}}$	14	16	18	dB	$f = 250 \text{ kHz}, R_E = 510 \Omega$	Fig. 12
Frequency characteristic	BW	3			MHz	$250 \text{ kHz} = 0 \text{ dB}, -3 \text{ dB}$	
Crosstalk DIFC1 $\leftrightarrow$ DIFC2	$G_{\text{CTLK}}$	45			dB	$f = 250 \text{ kHz}$	
Differentiator input resistance	$R_{\text{ID}}$	30			$\text{k}\Omega$		Fig. 13
Differentiator constants setting pin output resistance	$R_{\text{CD}}$		100		$\Omega$		Fig. 12
Differentiator constants setting pin current	$I_{\text{SINK}}$	0.5	0.75		$\text{mA}$		Fig. 14
Diff. output resistance	$R_{\text{OD}}$		50		$\Omega$		Fig. 12
Diff. output voltage amplitude	$V_{\text{OD}}$	2			$\text{V}_{\text{pk-pk}}$	Distortion rate = 5%	
Output sink current	$I_{\text{OSINK}}$	1.8	2.8		$\text{mA}$		Fig. 14

**Electrical characteristics (unless otherwise noted,  $T_a = 25^\circ\text{C}$ ,  $\text{AV}_{\text{CC}} = \text{DV}_{\text{CC}} = 5 \text{ V}$ ,  $\text{HV}_{\text{CC}} = 12 \text{ V}$ ) (Sheet 3 of 5)**

Parameter	Symbol	Min	Typical	Max	Unit	Conditions	Test circuit
<b>Comparator and pulse shaper</b>							
Differential input resistance	$R_{ID}$	10			$\text{k}\Omega$		Fig. 15
Max differential input voltage	$V_{IN \text{ max}}$	4			$V_{\text{pk-pk}}$		
TD monostable multivibrator pulse width adjustment range	$t_{rD}$	500		3000	ns		
TD monostable multivibrator pulse width accuracy (With Pin 37 (TDR2) open)	$E_{TD1}$	-20		+20	%	$R_{TD} = 200 \text{ k}\Omega$ , *( $t_{TD} \approx 2.35 \mu\text{s}$ )	
	$E_{TD2}$	-12		+12	%	$R_{TD} = 40 \text{ k}\Omega$ , $C_{TD} = 100 \text{ pF}$ , ( $t_{TD} \approx 2.35 \mu\text{s}$ )	
TD monostable multivibrator pulse width voltage dependency With Pin 37 (TDR2) open	$PSt_{rD1}$	-12	-5	+4	%/V	$R_{TD} = 200 \text{ k}\Omega$ , ( $t_{TD} \approx 2.35 \mu\text{s}$ )	
	$PSt_{rD2}$	-6	-1	+4	%/V	$R_{TD} = 40 \text{ k}\Omega$ , $C_{TD} = 100 \text{ pF}$	
RD monostable multivibrator pulse width adjustment range	$t_{RD}$	125		1500	ns		
RD monostable multivibrator pulse width accuracy	$E_{RD}$	-20		+20	%	$R_{RD} = 36 \text{ k}\Omega$ , $t_{RD} \approx 0.5 \mu\text{s}$	
RD monostable multivibrator pulse width voltage dependency	$PS_{tRD}$	-12	-2	+12	%/V	$R_{RD} = 36 \text{ k}\Omega$ , $t_{RD} \approx 0.5 \mu\text{s}$	
Rise time	$t_{TLH}$			70	ns		
Fall time	$t_{THL}$			25	ns		
Peak shift	PS			1	%	$V_{IN} = 0.15 \sim 2 \text{ V}_{\text{pk-pk}}$	
Low level output voltage	$V_{OL}$			0.5	V	$I_{OL} = 2 \text{ mA}$	
High level output voltage	$V_{OH}$	2.7			V	$I_{OH} = -0.4 \text{ mA}$	Fig. 16

Fig. 17

## BA6589K Floppy disk drives: Read/write amplifier

**Electrical characteristics (unless otherwise noted,  $T_a = 25^\circ\text{C}$ ,  $\text{AV}_{CC} = \text{DV}_{CC} = 5 \text{ V}$ ,  $\text{HV}_{CC} = 12 \text{ V}$ ) (Sheet 4 of 5)**

Parameter	Symbol	Min	Typical	Max	Unit	Conditions	Test circuit
<b>Write circuit</b>							
Write current adjustment range	IWR	2		20	mA	Includes LC and HD pin correction currents. See note 1 on page 250	Fig. 18
Corrected write current adjustment range	IWC			5	mA	At LC and HD pin	
Write current accuracy	ACl <sub>W</sub>	-7		+7	%	$I_{WR} = 6 \text{ mA}$ , $R_{WCSO} = 1.9 \text{ k}\Omega$	
Write current mismatch	$\Delta I_{WR}$	-2		+2	%	$R_{WCSO} = 1.9 \text{ k}\Omega$	
Write current supply voltage dependency	PSI <sub>W</sub>	-4	-2	+1	%/V	$R_{WCSO} = 1.9 \text{ k}\Omega$	
Output saturation voltage	V <sub>SATRW</sub>		1.3	1.8	V	With Pin 37 (TDR2) open	
Off state leakage current	I <sub>LKRW1</sub>			20	μA	Deselected side, $V_{RW} = 14 \text{ V}$ . With Pin 37 (TDR2) open	Fig. 18
	I <sub>LKRW2</sub>			50	μA	Selected side, $V_{RW} = 14 \text{ V}$ $V_{RW}$ pin when output voltage set for $I_W$ of 12 mA and decreased slowly to 10.8 mA	
Write data min pulse width	t <sub>WD</sub>	70			ns		Fig. 19
Timing balance	ΔI <sub>W</sub>			0.5	%	f = 500 kHz	Fig. 18
<b>Erase output</b>							
Erase current adjustment range	I <sub>ER</sub>	5		100	mA		Fig. 20
Output saturation voltage	V <sub>SATER</sub>		0.8	1.4	V	$I_{ER} = 100 \text{ mA}$ , $R_{ECSO} = 1.8 \text{ k}\Omega$	
Output leakage current	I <sub>OH</sub>			100	μA	$V_{OH} = 20 \text{ V}$	

**Electrical characteristics (unless otherwise noted,  $T_a = 25^\circ\text{C}$ ,  $\text{AV}_{\text{CC}} = \text{DV}_{\text{CC}} = 5\text{ V}$ ,  $\text{HV}_{\text{CC}} = 12\text{ V}$ ) (Sheet 5 of 5)**

Parameter	Symbol	Min	Typical	Max	Unit	Conditions	Test circuit
<b>Logic inputs</b>							
High level input voltage 1	$V_{IH1}$	2			V	LC, HD, TD <sub>FC</sub> , PS	Fig. 21
Low level input voltage 2	$V_{IL1}$			0.8	V	LC, HD, TD <sub>FC</sub> , PS	
High level input voltage 1	$V_{IH2}$	2			V	WG, EG, S1	
Low level input voltage 2	$V_{IL2}$			0.8	V	WG, EG, S1	
Input volt hysteresis 2	$V_{H2}$	0.2			V	WG, EG, S1	
High level input voltage 3	$V_{IH3}$	2			V	WD	
Low level input voltage 3	$V_{IL3}$			0.7	V	WD	
Input volt hysteresis 3	$V_{H3}$	0.2			V	WD	
High level input current 1	$I_{IH1}$			10	$\mu\text{A}$	LC, HD, TD <sub>FC</sub> , PS $V_{OH} = 2.8\text{ V}$	
Low level input current 1	$I_{IL1}$			40	$\mu\text{A}$	LC, HD, TD <sub>FC</sub> , PS $V_{OL} = 0.4\text{ V}$	
High level input current 2	$I_{IH2}$			10	$\mu\text{A}$	WG, EG, S1, $V_{OH} = 2.8\text{ V}$	
Low level input current 2	$I_{IL2}$			40	$\mu\text{A}$	WG, EG, S1, $V_{OL} = 0.4\text{ V}$	
High level input current 3	$I_{IH3}$			10	$\mu\text{A}$	WD, $V_{OH} = 2.8\text{ V}$	
Low level input current 3	$I_{IL3}$			400	$\mu\text{A}$	WD, $V_{OL} = 0.4\text{ V}$	

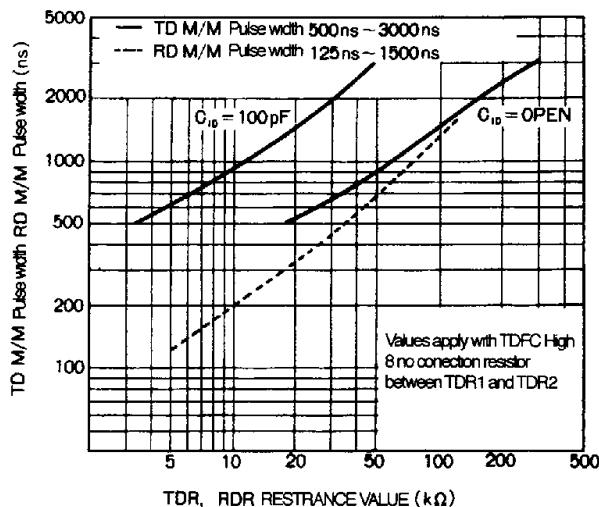
The pin used to set the time domain filter TD monostable multivibrator pulse width (TDR1) has an internal capacitance of 15 pF. Therefore, the TD monostable multivibrator pulse width can be set using  $R_{TD}$  only. ( $R_{TD}$  is the external resistor used to pull-up the TDR1 pin to AVCC).

If this method is used, when TD<sub>FC</sub> is HIGH (no correction), the TD monostable multivibrator pulse width will have frequency characteristics due to the internal capacitance of the TDR2 pin.

The effect of the internal capacitance of pin TDR2 can be reduced by inserting a 100 pF capacitor,  $C_{TD}$ , between the TDR1 pin and GND, to adjust the time constant. This will ensure that the TD monostable multivibrator pulse width does not vary with frequency. It will also reduce the influence of the 15 pF internal capacitance at TDR1, thus improving the accuracy of the TD monostable multivibrator pulse width timing.

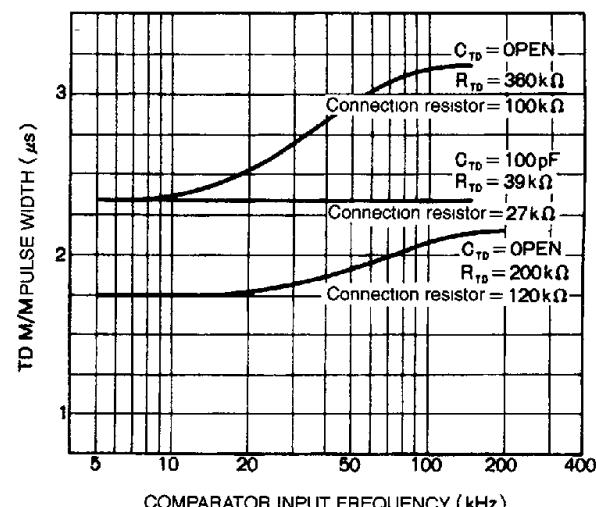
## BA6589K Floppy disk drives: Read/write amplifier

Figure 2 shows the TD min/max pulse width against comparator input frequency when the value of  $C_{TD}$  is 100 pF, and when it is not in the circuit.



Values are for TDFC = HIGH and no resistor between TDR1 and TDR2

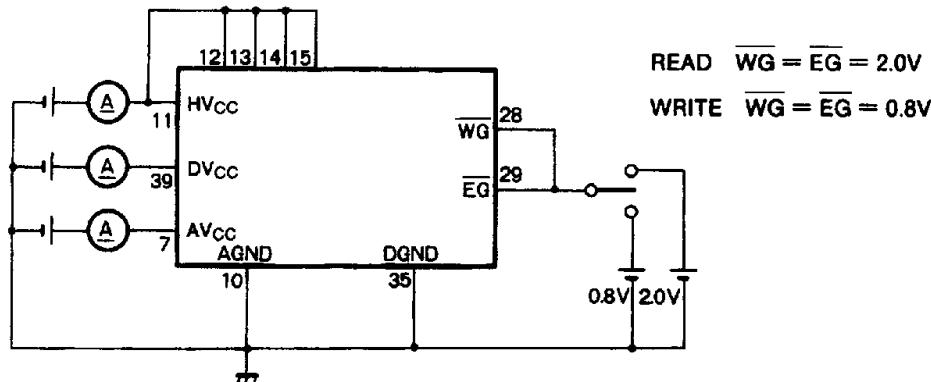
**Figure 1 Time domain filter**



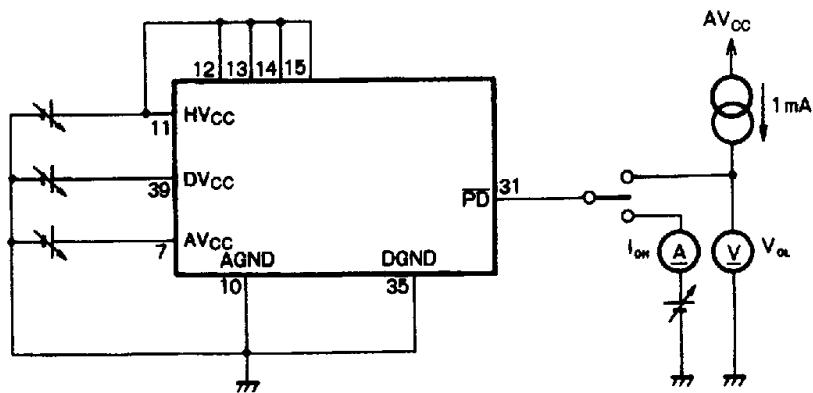
Values are for TDFC = HIGH

**Figure 2**

## Test circuits



**Figure 3 Supply current:  $I_{CCHS}$ ,  $I_{CCHR}$ ,  $I_{CCHW}$ ,  $I_{CCDS}$ ,  $I_{CCDR}$ ,  $I_{CCDW}$ ,  $I_{CCAS}$ ,  $I_{CCAR}$ ,  $I_{CCAW}$  test circuit**



MONITOR  $I_{WR}$  (RW 00, RW 01, RW 10, RW 11)

$I_{ER}$  (E00, E01)

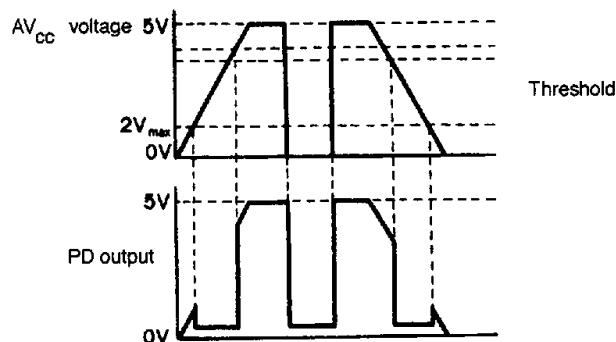
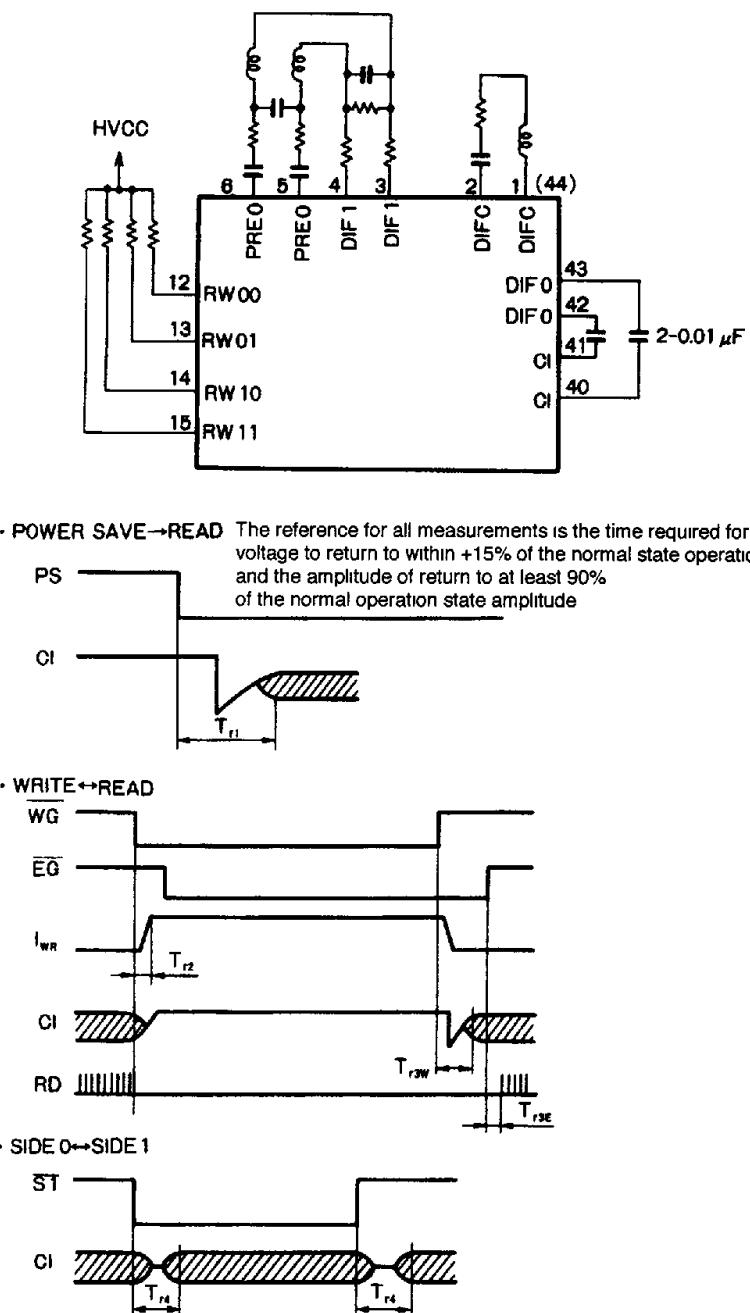
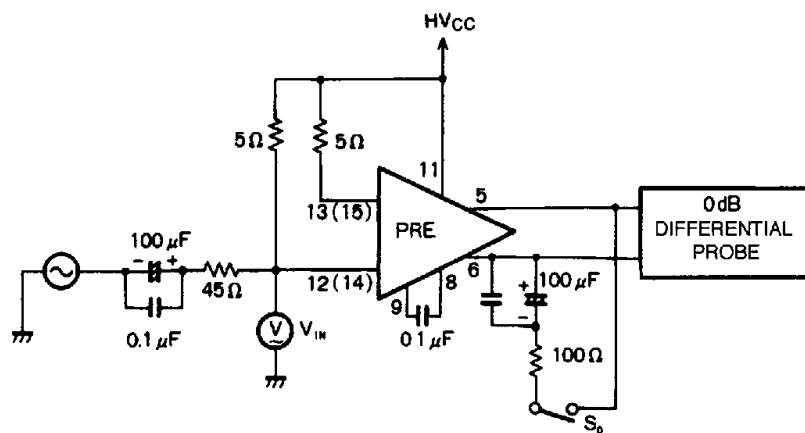


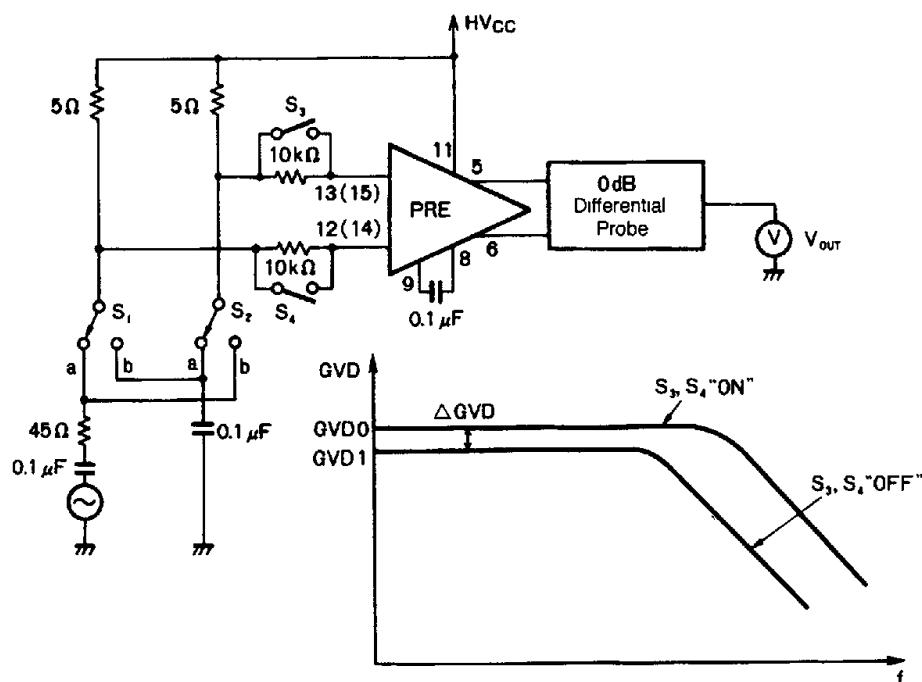
Figure 4 Power down (LVS at AV<sub>CC</sub>): V<sub>TH</sub>, V<sub>H</sub>, V<sub>OL</sub>, I<sub>OH</sub> test circuit



**Figure 5 Recovery time:  $T_{r1}$ ,  $T_{r2}$ ,  $T_{r3W}$ ,  $T_{r3E}$ ,  $T_{r4}$  test circuit**



**Figure 6 Preamplifier:  $G_{VD}$ , BW,  $G_{CTLK}$ ,  $V_{INmax}$ ,  $V_{OD}$ ,  $R_{OD}$  test circuit**



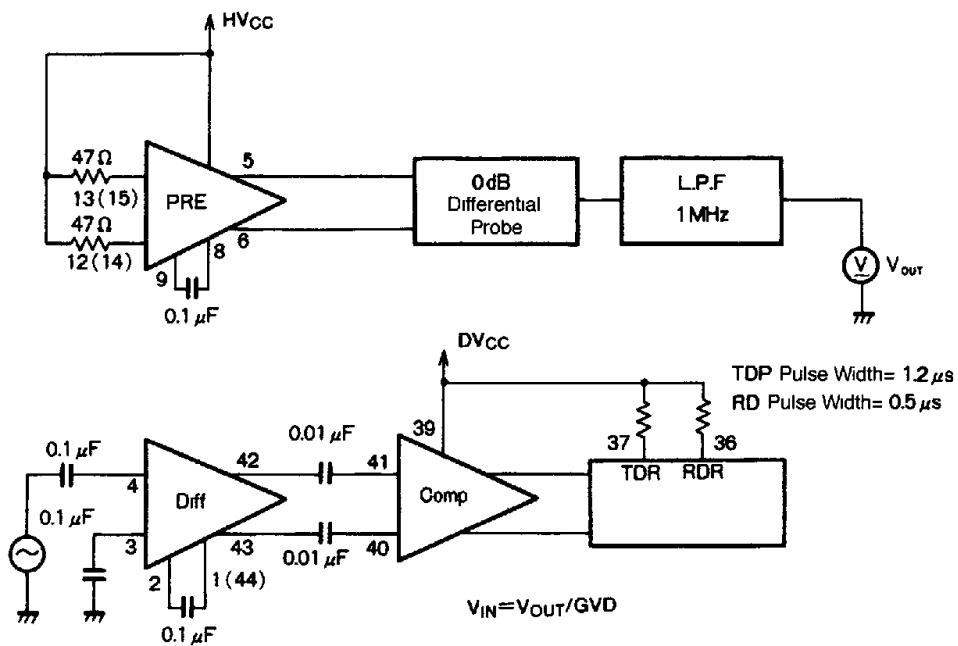
$$R_{ID} = \left( \frac{10^{-\Delta GVDa/20}}{1 - 10^{-\Delta GVDa/20}} + \frac{10^{-\Delta GVDb/20}}{1 - 10^{-\Delta GVDb/20}} \right) \times 1Q [k\Omega]$$

$\Delta GVDa$  = GVD (in dB) when  $S_3$  and  $S_4$  are in the "a" position

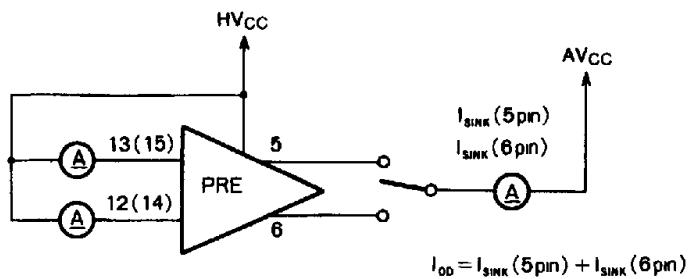
$\Delta GVDb$  = GVD (in dB) when  $S_3$  and  $S_4$  are in the "b" position

**Figure 7 Differential input resistance test circuit**

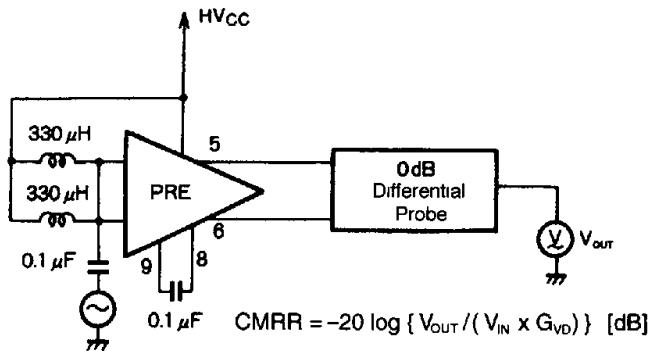
## BA6589K Floppy disk drives: Read/write amplifier



**Figure 8 Input conversion noise voltage:  $V_{N1}$ ,  $V_{N2}$  test circuit**



**Figure 9 Input sink current  $I_{SINK}$  and diff output current amplitude  $I_{OD}$  test circuit**



**Figure 10 Common mode rejection ratio (CMRR) test circuit**

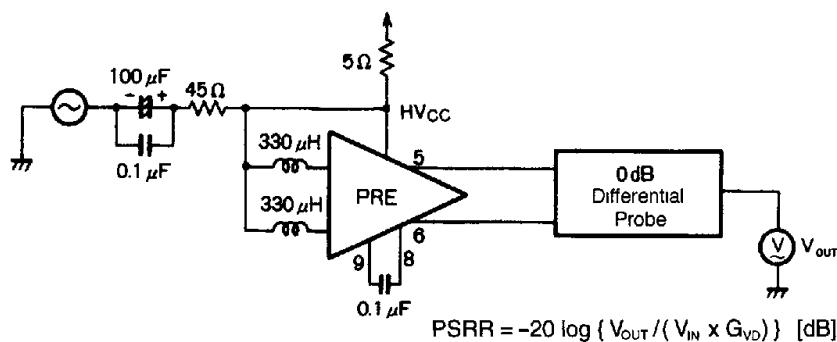


Figure 11 Power supply rejection ratio (PSRR) test circuit

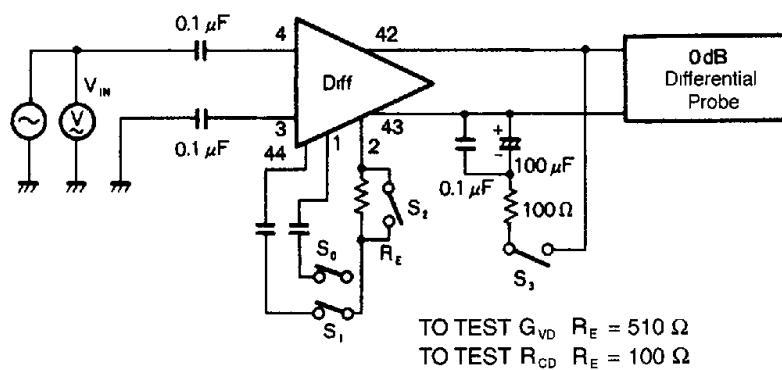
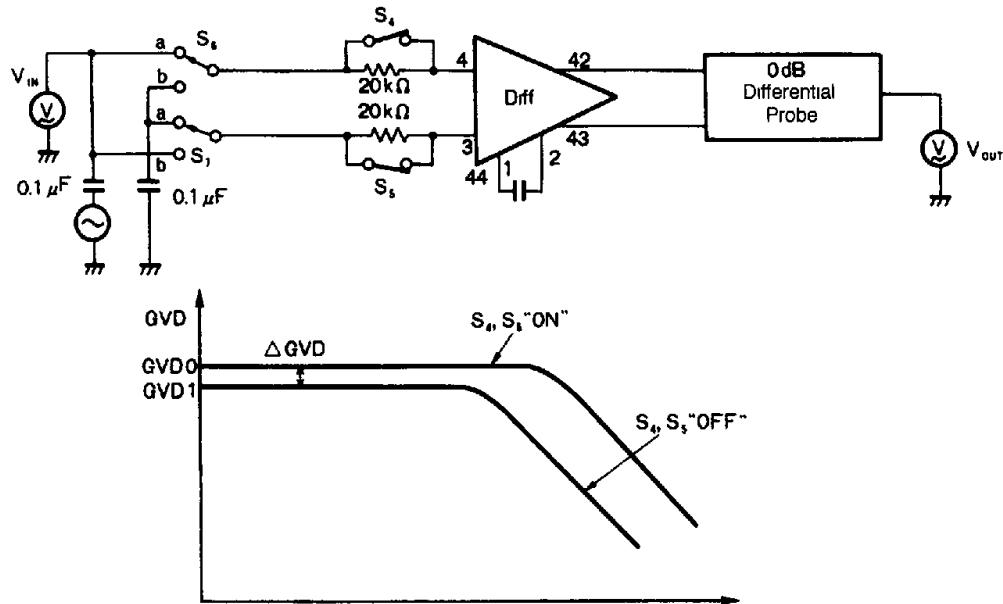


Figure 12 Differentiator: GVD, BW, G<sub>CTLK</sub>, R<sub>CD</sub>, V<sub>OD</sub>, R<sub>OD</sub> test circuit

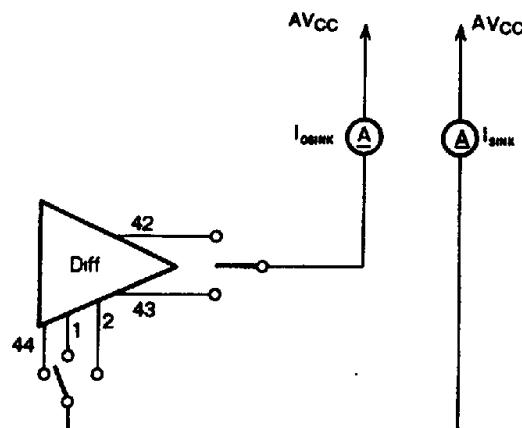


$$R_{ID} = \left( \frac{10^{-\Delta GVDa/20}}{1 - 10^{-\Delta GVDa/20}} + \frac{10^{-\Delta GVDb/20}}{1 - 10^{-\Delta GVDb/20}} \right) \times 1Q [k\Omega]$$

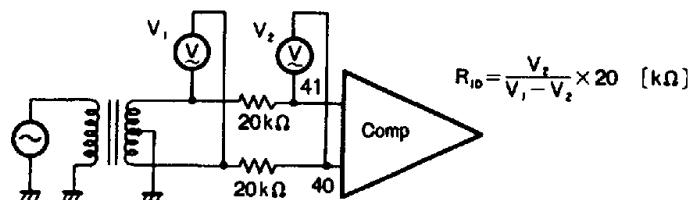
$\Delta GVDa$  = GVD (indB) when S<sub>6</sub> and S<sub>7</sub> are in the "a" position  
 $\Delta GVDb$  = GVD (indB) when S<sub>6</sub> and S<sub>7</sub> are in the "b" position

Figure 13 Differential input resistance R<sub>ID</sub> test circuit

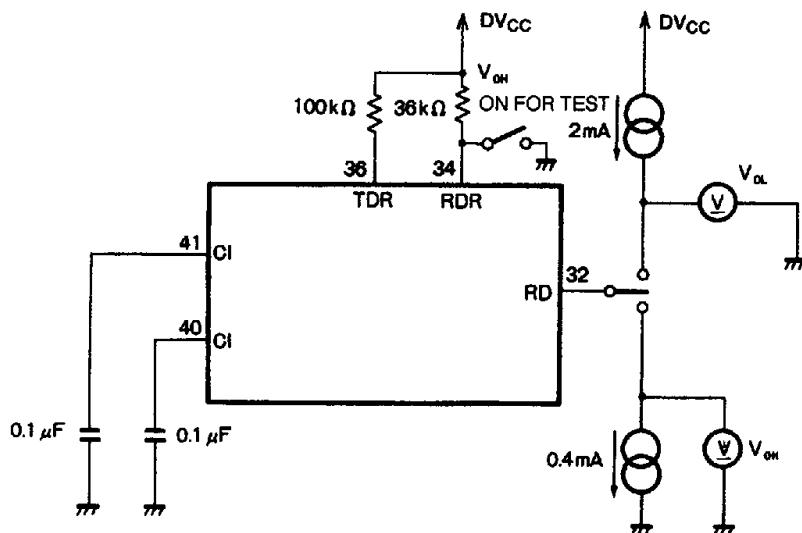
## BA6589K Floppy disk drives: Read/write amplifier



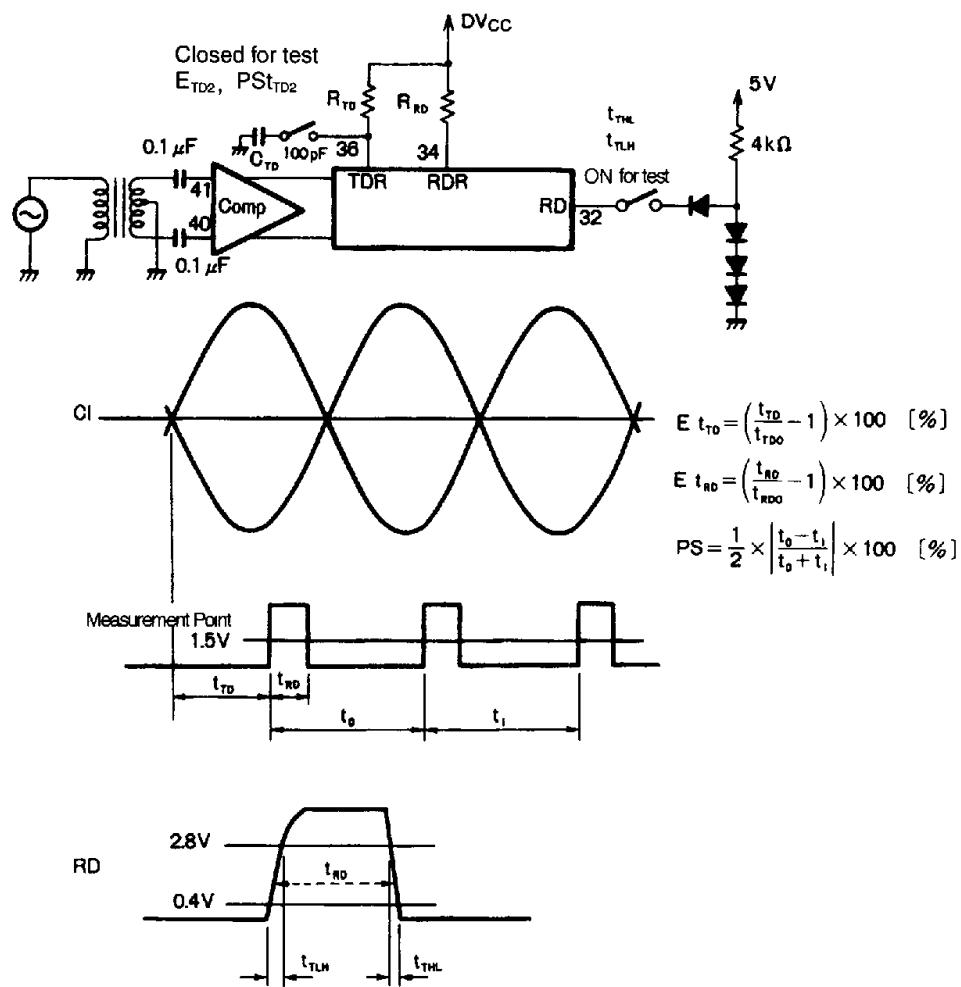
**Figure 14** Differentiator constant, pin current & output sink current test circuit



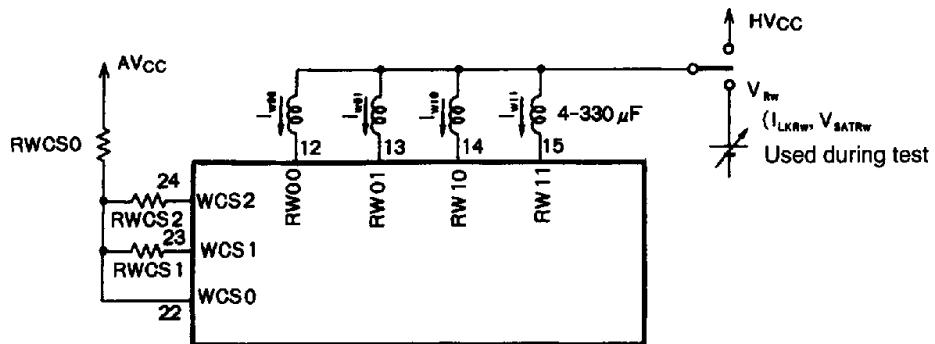
**Figure 15** Comparator: Diff input resistance ( $R_{ID}$ ) test circuit



**Figure 16** Comparator time domain filter:  $V_{OH}$ ,  $V_{OL}$  test circuit



**Figure 17 Comparator time domain filter:  $V_{INmax}$ ,  $t_{TD}$ ,  $E_{TD}$ ,  $t_{RD}$ ,  $E_{RD}$ , and PS test circuit**



Write current equation

$$I_{WR} = |I_{W00} - I_{W01}| \quad (SI = H) \\ |I_{W10} - I_{W11}| \quad (SI = L)$$

Equation for setting write current

$$I_{WRO} = \frac{1.22V}{RWCS0} \times 9.6$$

Equations for setting write correction current

$$I_{WC1O} = \frac{1.22V - V_{WCS}}{RWCS_1} \times 9.6 \quad V_{WCS1} : \text{Voltage between } AV_{CC} - \text{WCS1 controlled by (LC)}$$

$$I_{WC2O} = \frac{1.22V - V_{WCS_2}}{RWCS2} \times 9.6 \quad V_{WCS2} : \text{Voltage between } AV_{CC} - \text{WCS2 controlled by (HD)}$$

$$ACl_W = \frac{I_{WR} - 6(\text{mA})}{6(\text{mA})} \times 100 \quad RWCS0 = 1.91k\Omega$$

$$\Delta I_{WR} = \frac{2 |I_{W00} - I_{W01}|}{|I_{W00} + I_{W01}|} \times 100$$

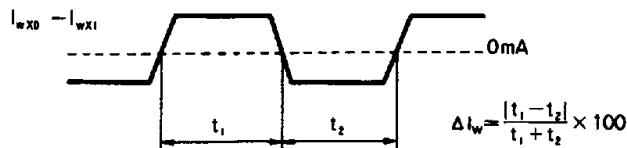
$$= \frac{2 |I_{W10} - I_{W11}|}{|I_{W10} + I_{W11}|} \times 100$$

$$PSIW = \frac{2 |I_{WH} - I_{WL}|}{|I_{WH} + I_{WL}|} \times \frac{1}{1.6}$$

$I_{WH}$  : Write current at  $AV_{CC}=6.0V$

$I_{WL}$  : Write current at  $AV_{CC}=4.4V$

**Figure 18 Write circuit:  $I_{WR}$ ,  $ACl_W$ ,  $\Delta I_{WR}$ ,  $V_{SATRW}$ ,  $I_{LKRW}$ ,  $I_{WC}$ ,  $L_{RWOFF}$  test circuit**



**Figure 19 Write circuit:  $\Delta I_W$ ,  $t_{WD}$  waveforms**

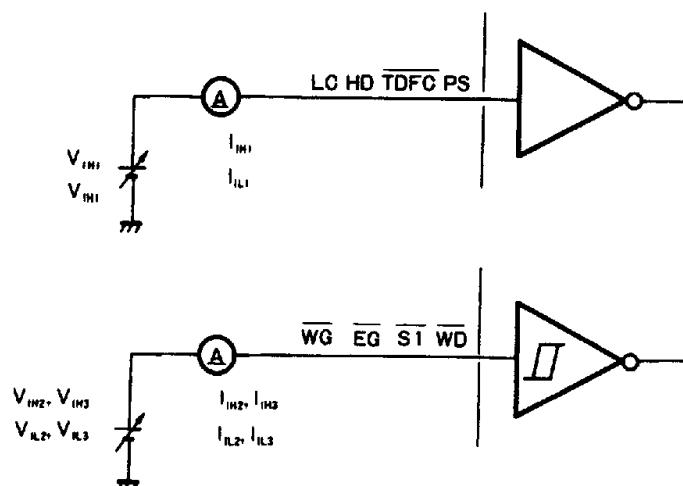
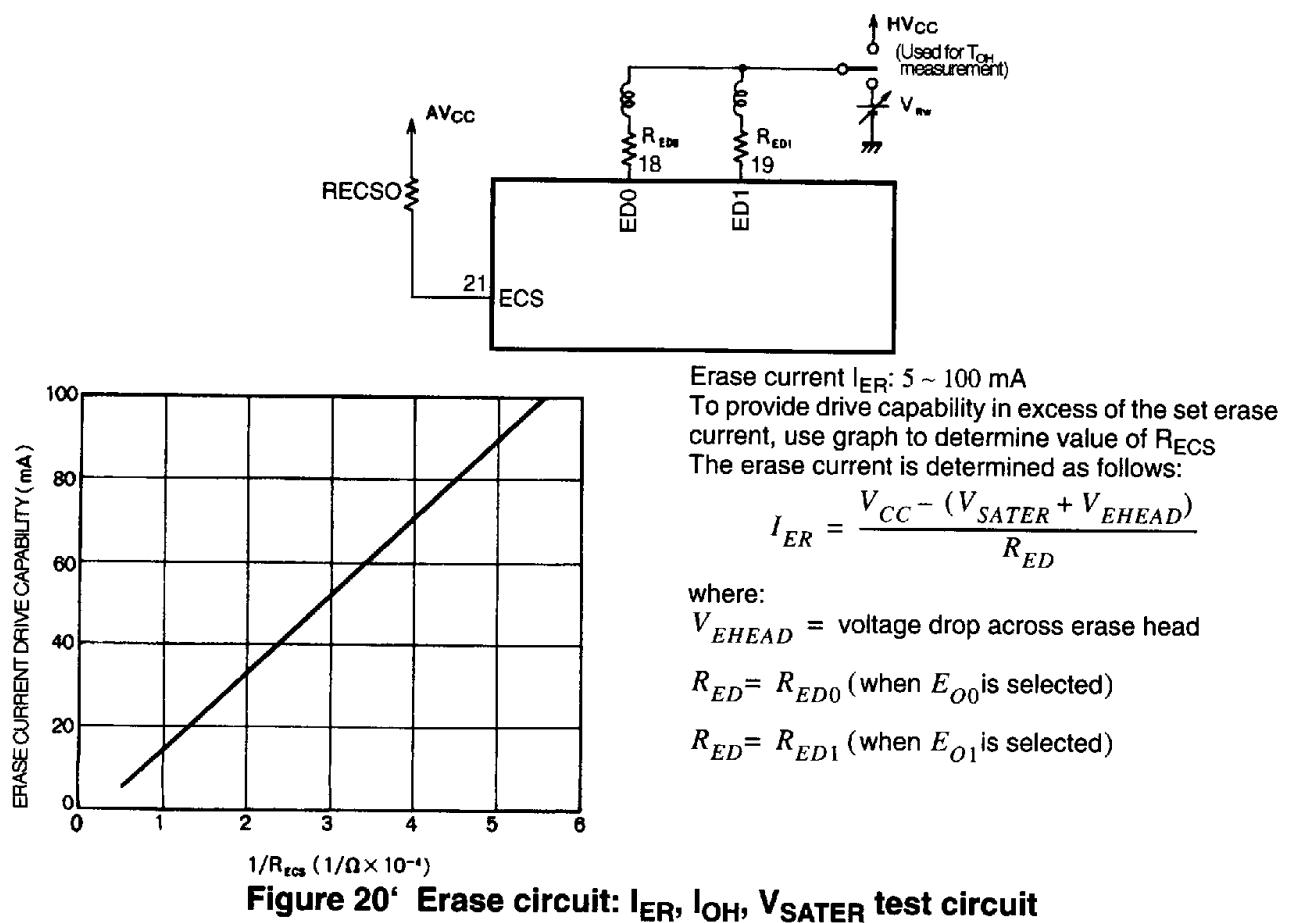


Figure 21 Control logic:  $V_{IH}$ ,  $V_{IL}$ ,  $V_H$ ,  $I_{IH}$ , &  $I_{IL}$  test circuit